

Abstract

It is provided a method of growing gallium nitride single crystal of good quality with a high productivity, in the growth of gallium nitride single crystal by Na-flux method. Gallium nitride single crystal is grown using flux 8 containing at least sodium metal. Gallium nitride single crystal is grown in atmosphere composed of gases mixture "B" containing nitrogen gas at a pressure of 300 atms or higher and 2000 atms or lower. Preferably, the nitrogen partial pressure in the atmosphere is 100 atms or higher and 2000 atms or lower. Preferably, the growth temperature is 1000 °C or higher and 1500 °C or lower.